

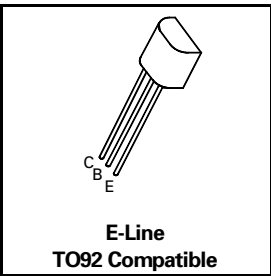
# PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

**ZTX752  
ZTX753**

ISSUE 2 – JULY 94

## FEATURES

- \* 100 Volt  $V_{CE0}$
- \* 2 Amp continuous current
- \* Low saturation voltage
- \*  $P_{tot}=1$  Watt



## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX752	ZTX753	UNIT
Collector-Base Voltage	$V_{CBO}$	-100	-120	V
Collector-Emitter Voltage	$V_{CEO}$	-80	-100	V
Emitter-Base Voltage	$V_{EBO}$		-5	V
Peak Pulse Current	$I_{CM}$		-6	A
Continuous Collector Current	$I_C$		-2	A
Power Dissipation at $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	$P_{tot}$		1 5.7	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j; T_{stg}$		-55 to +200	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	ZTX752			ZTX753			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-100			-120			V	$I_C=-100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80			-100			V	$I_C=-10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			-5			V	$I_E=-100\mu A$
Collector Cut-Off Current	$I_{CBO}$			-0.1 -10			-0.1 -10	$\mu A$ $\mu A$ $\mu A$ $\mu A$	$V_{CB}=-80V$ $V_{CB}=-100V$ $V_{CB}=-80V, T_{amb}=100^{\circ}C$ $V_{CB}=-100V, T_{amb}=100^{\circ}C$
Emitter Cut-Off Current	$I_{EBO}$			-0.1			-0.1	$\mu A$	$V_{EB}=-4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.17 -0.30	-0.3 -0.5			-0.17 -0.30 -0.5	V V	$I_C=-1A, I_B=-100mA^*$ $I_C=-2A, I_B=-200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.25			-0.9 -1.25	V	$I_C=-1A, I_B=-100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1			-0.8 -1	V	$I_C=-1A, V_{CE}=-2V^*$

# ZTX752 ZTX753

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ ).

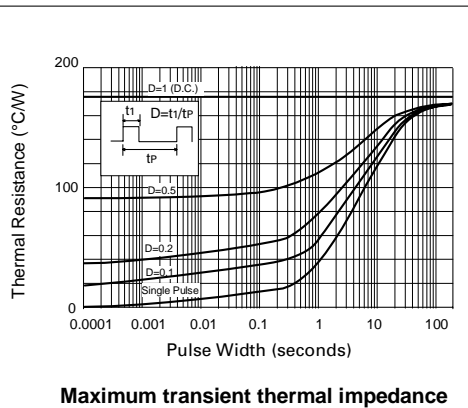
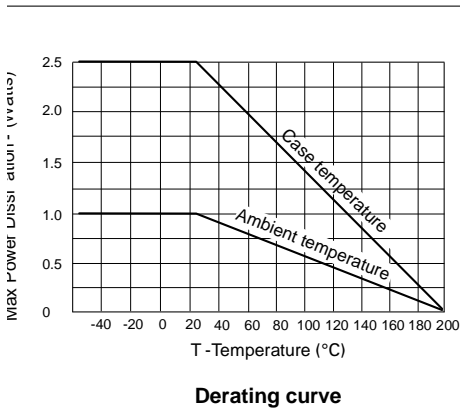
PARAMETER	SYMBOL	ZTX752			ZTX753			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Transition Frequency	$f_T$	100	140		100	140		MHz	$I_C = -100\text{mA}$ , $V_{CE} = -5\text{V}$ $f = 100\text{MHz}$
Switching Times	$t_{on}$		40			40		ns	$I_C = -500\text{mA}$ , $V_{CC} = -10\text{V}$ $I_{B1} = I_{B2} = -50\text{mA}$
	$t_{off}$		600			600		ns	
Output Capacitance	$C_{obo}$			30			30	pF	$V_{CB} = 10\text{V}$ $f = 1\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

## THERMAL CHARACTERISTICS

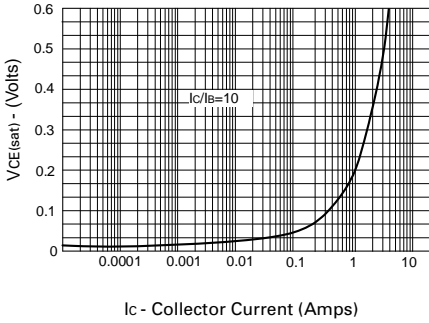
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient <sub>1</sub>	$R_{th(j-amb)1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient <sub>2</sub>	$R_{th(j-amb)2} \dagger$	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

$\dagger$  Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

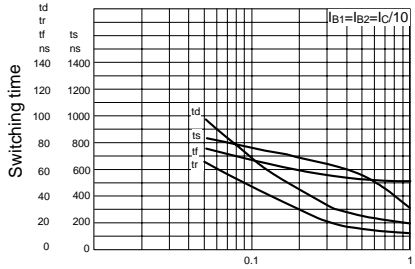


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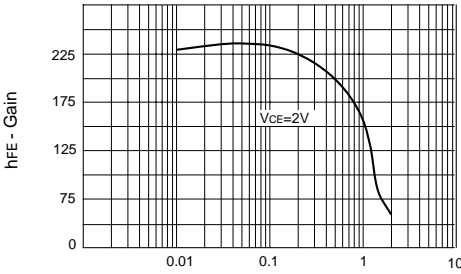
## TYPICAL CHARACTERISTICS



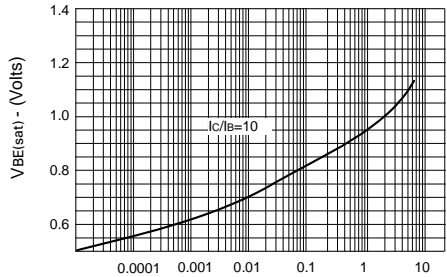
**$V_{CE(sat)}$  v  $I_C$**



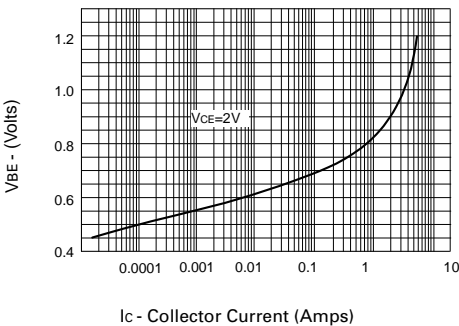
**Switching Speeds**



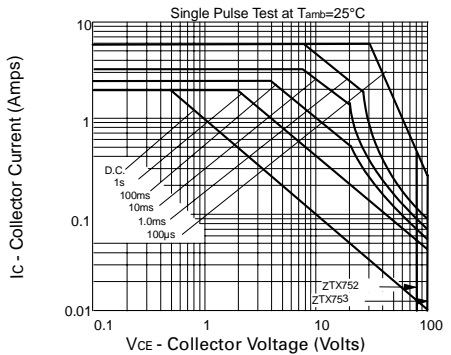
**$h_{FE}$  v  $I_C$**



**$V_{BE(sat)}$  v  $I_C$**



**$V_{BE(on)}$  v  $I_C$**



**Safe Operating Area**